

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor IPD60R800CE,IIPD60R800CE

FEATURES Static drain-source on-resistance:

- Ros(on)≤0.8Ω
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

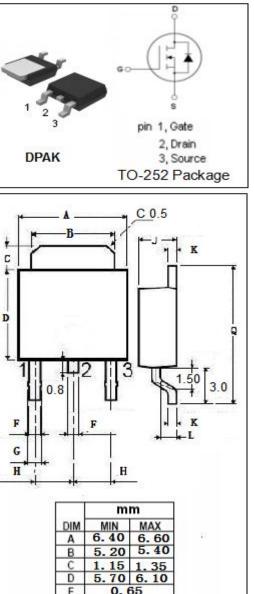
DESCRITION

· Fast switching

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)			
SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	±20	V
ΙD	Drain Current-Continuous	8.4	А
I _{DM}	Drain Current-Single Pulsed	15.7	А
PD	Total Dissipation @T _c =25°C	74	W
Tj	Max. Operating Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT	
Rth(j-c)	Channel-to-case thermal resistance	1.7	°C/W	
Rth(j-a)	Rth(j-a) Channel-to-ambient thermal resistance		°C/W	



0.

50

40

10

0.60

10

2.10

2.10

0.40

0.90

9.90

G

н

K

0



isc N-Channel MOSFET Transistor

IPD60R800CE,IIPD60R800CE

ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =0.25mA	600			v
V _{GS} (th)	Gate Threshold Voltage	VDS=VGS; ID=0.17mA	2.5		3.5	v
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =2A			0.8	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V; V _{DS} =0V			0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V			1	μA
V _{SD}	Diode forward voltage	I _F =2.5A, V _{GS} = 0V		0.9		V

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